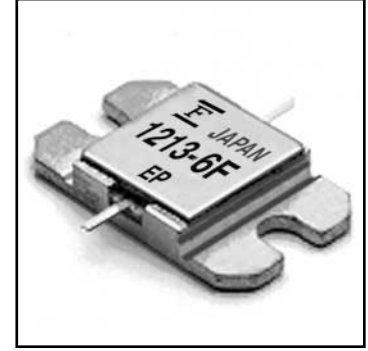


FEATURES

- High Output Power: $P_{1dB} = 37.5\text{dBm}$ (Typ.)
- High Gain: $G_{1dB} = 7.0\text{dB}$ (Typ.)
- High PAE: $\eta_{add} = 27\%$ (Typ.)
- Low $IM_3 = -45\text{dBc}$ @ $P_o = 25\text{dBm}$
- Broad Band: 12.7 ~ 13.2GHz
- Impedance Matched $Z_{in}/Z_{out} = 50\Omega$
- Hermetically Sealed

DESCRIPTION

The FLM1213-6F is a power GaAs FET that is internally matched for standard communication bands to provide optimum power and gain in a 50 ohm system.



Fujitsu's stringent Quality Assurance Program assures the highest reliability and consistent performance.

ABSOLUTE MAXIMUM RATING (Ambient Temperature $T_a = 25^\circ\text{C}$)

Item	Symbol	Condition	Rating	Unit
Drain-Source Voltage	V_{DS}		15	V
Gate-Source Voltage	V_{GS}		-5	V
Total Power Dissipation	P_T	$T_C = 25^\circ\text{C}$	31.2	W
Storage Temperature	T_{stg}		-65 to +175	$^\circ\text{C}$
Channel Temperature	T_{ch}		175	$^\circ\text{C}$

Fujitsu recommends the following conditions for the reliable operation of GaAs FETs:

1. The drain-source operating voltage (V_{DS}) should not exceed 10 volts.
2. The forward and reverse gate currents should not exceed 26.0 and -2.8 mA respectively with gate resistance of 100Ω .

ELECTRICAL CHARACTERISTICS (Ambient Temperature $T_a = 25^\circ\text{C}$)

Item	Symbol	Test Conditions	Limit			Unit
			Min.	Typ.	Max.	
Saturated Drain Current	I_{DSS}	$V_{DS} = 5\text{V}, V_{GS} = 0\text{V}$	-	2800	4200	mA
Transconductance	g_m	$V_{DS} = 5\text{V}, I_{DS} = 1800\text{mA}$	-	2350	-	mS
Pinch-off Voltage	V_p	$V_{DS} = 5\text{V}, I_{DS} = 120\text{mA}$	-0.5	-1.5	-3.0	V
Gate Source Breakdown Voltage	V_{GSO}	$I_{GS} = -120\mu\text{A}$	-5	-	-	V
Output Power at 1dB G.C.P.	P_{1dB}	$V_{DS} = 10\text{V}$ $f = 12.7 \sim 13.2\text{GHz}$ $I_{DS} = 0.65 I_{DSS}(\text{Typ.})$ $Z_S = Z_L = 50\Omega$	36.5	37.5	-	dBm
Power Gain at 1dB G.C.P.	G_{1dB}		6.0	7.0	-	dB
Drain Current	I_{dsr}		-	1800	2100	mA
Power-Added Efficiency	η_{add}		-	27	-	%
Gain Flatness	ΔG		-	-	± 0.6	dB
3rd Order Intermodulation Distortion	IM_3	$f = 13.2\text{GHz}, \Delta f = 10\text{MHz}$ 2-Tone Test $P_{out} = 25\text{dBm S.C.L.}$	-42	-45	-	dBc
Thermal Resistance	R_{th}	Channel to Case	-	4.0	4.5	$^\circ\text{C/W}$

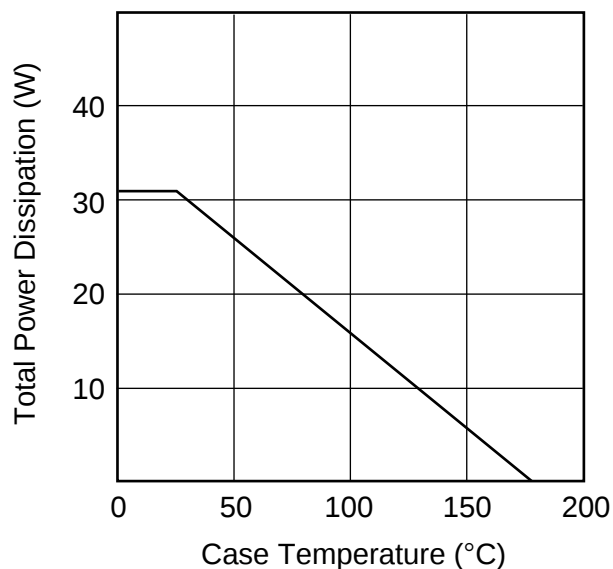
CASE STYLE: IA

G.C.P.: Gain Compression Point

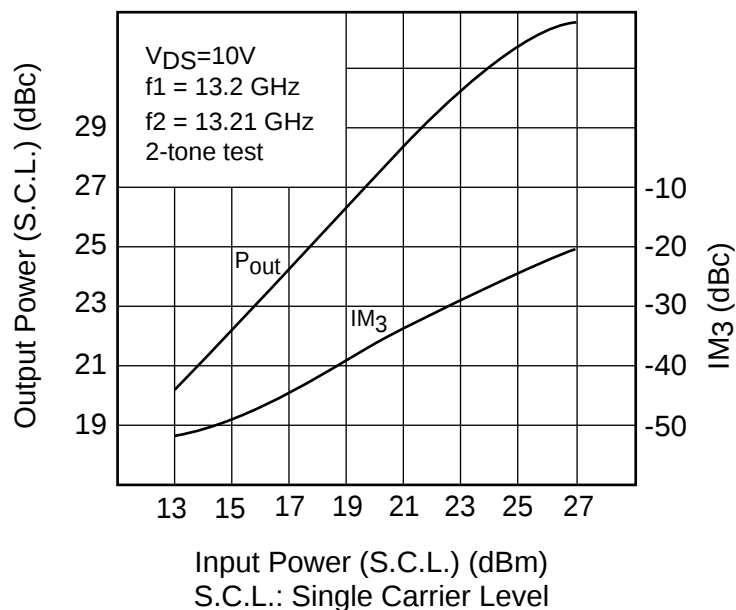
FLM1213-6F

X, Ku-Band Internally Matched FET

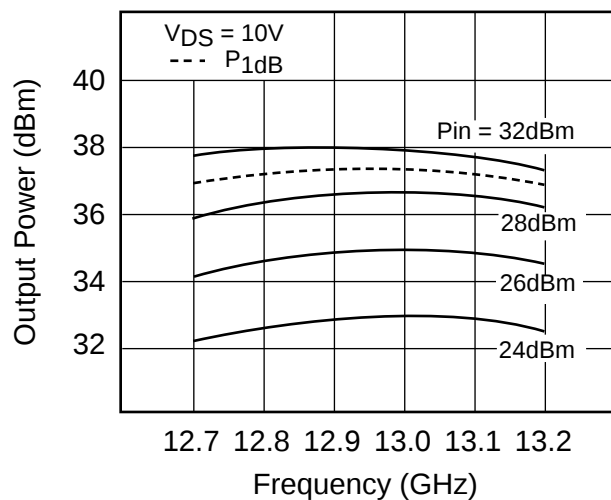
POWER DERATING CURVE



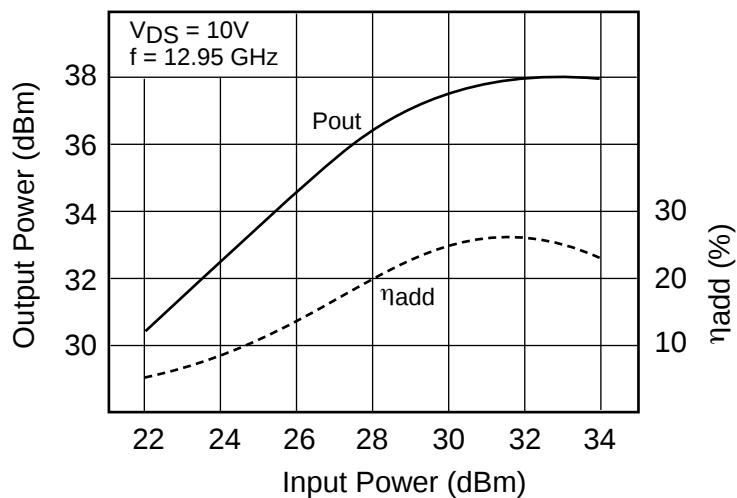
OUTPUT POWER & IM₃ vs. INPUT POWER

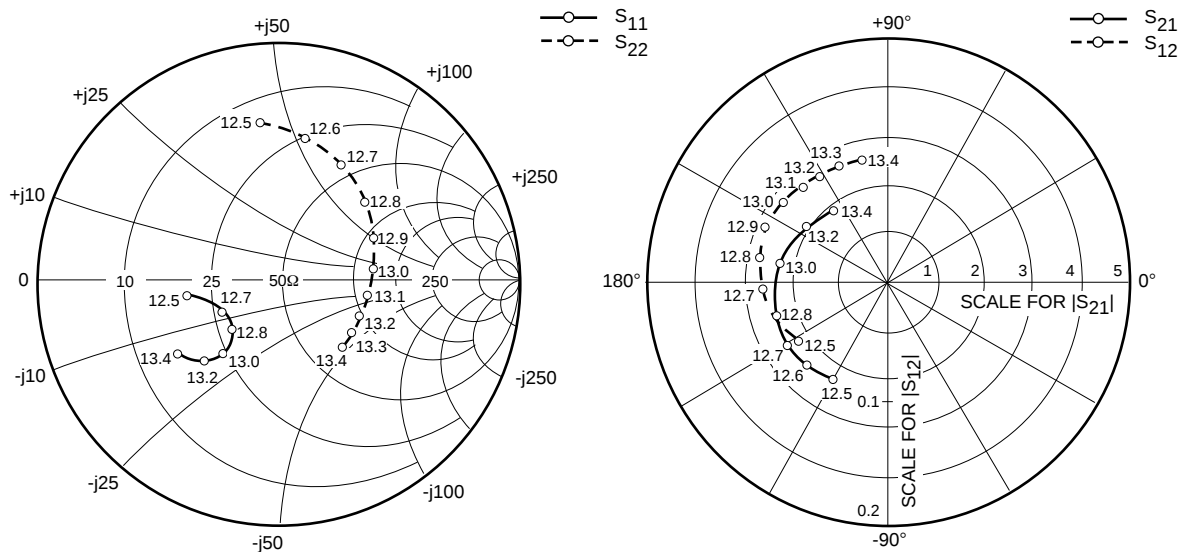


OUTPUT POWER vs. FREQUENCY



OUTPUT POWER vs. INPUT POWER





S-PARAMETERS

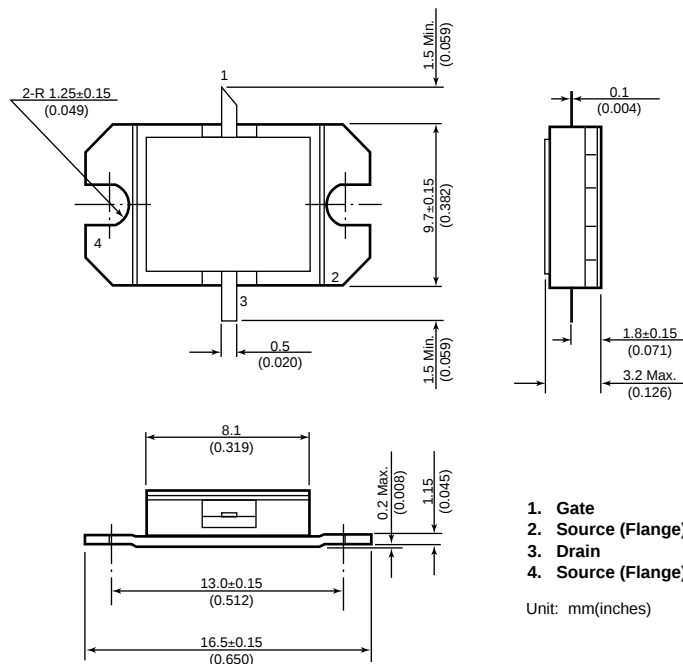
$V_{DS} = 10V$, $I_{DS} = 1800mA$

FREQUENCY (MHZ)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
12500	.363	-170.0	2.314	-120.0	.089	-147.7	.666	96.7
12600	.292	-162.8	2.423	-134.4	.098	-162.0	.605	79.7
12700	.259	-147.8	2.485	-149.4	.106	-177.7	.549	61.7
12800	.283	-134.2	2.462	-163.9	.109	167.6	.483	42.8
12900	.331	-127.7	2.388	-177.9	.111	154.2	.430	23.9
13000	.381	-127.4	2.291	169.6	.111	142.7	.398	6.7
13100	.426	-130.4	2.171	157.7	.108	131.1	.374	-10.3
13200	.467	-133.5	2.065	146.3	.107	121.0	.365	-24.0
13300	.493	-138.1	1.948	136.7	.106	112.3	.373	-37.4
13400	.509	-143.1	1.858	126.8	.105	102.8	.386	-47.0

FLM1213-6F

X, Ku-Band Internally Matched FET

Case Style "IA" Metal-Ceramic Hermetic Package



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- Do not put these products into the mouth.
- Do not alter the form of this product into a gas, powder, or liquid through burning, crushing, or chemical processing as these by-products are dangerous to the human body if inhaled, ingested, or swallowed.
- Observe government laws and company regulations when discarding this product. This product must be discarded in accordance with methods specified by applicable hazardous waste procedures.

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Printed in U.S.A. FCSI0598M200

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